

# SOT-23 Plastic-Encapsulate Transistors

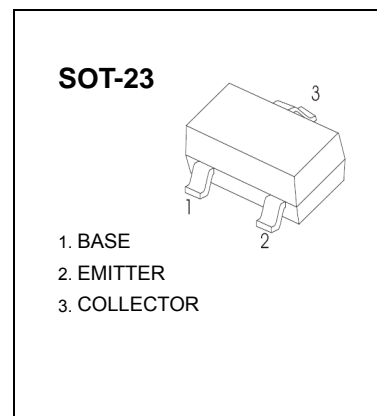
## 2SC1623 TRANSISTOR (NPN)

### FEATURES

- High DC current gain : $h_{FE}=200(\text{Typ})$   $V_{CE}=6V, I_C=1\text{mA}$
- High voltage: $V_{CEO}=50V$

### MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	60	V
$V_{CEO}$	Collector-Emitter Voltage	50	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current -Continuous	100	mA
$P_C$	Collector Power Dissipation	200	mW
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55-150	$^\circ\text{C}$



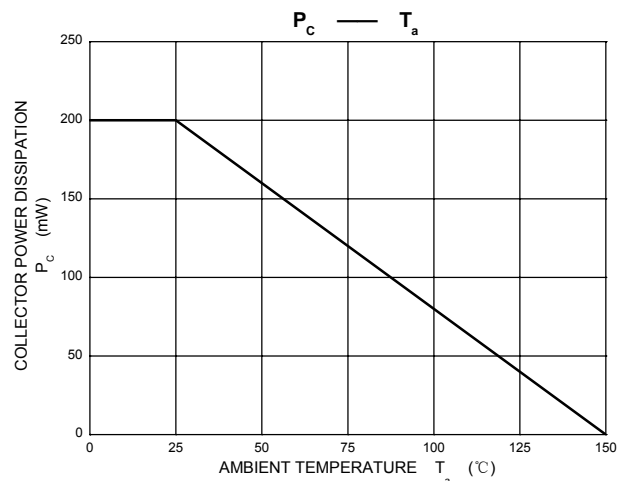
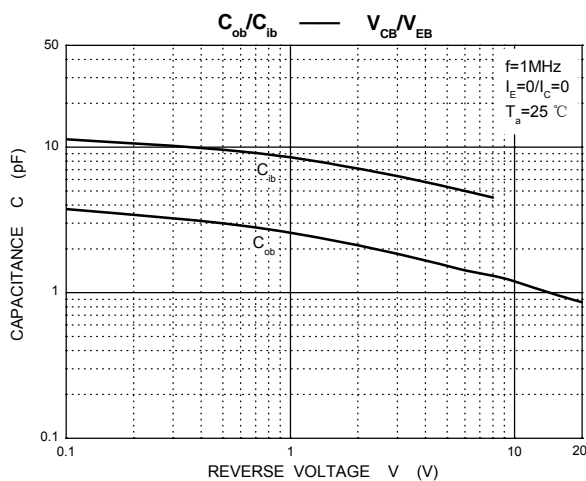
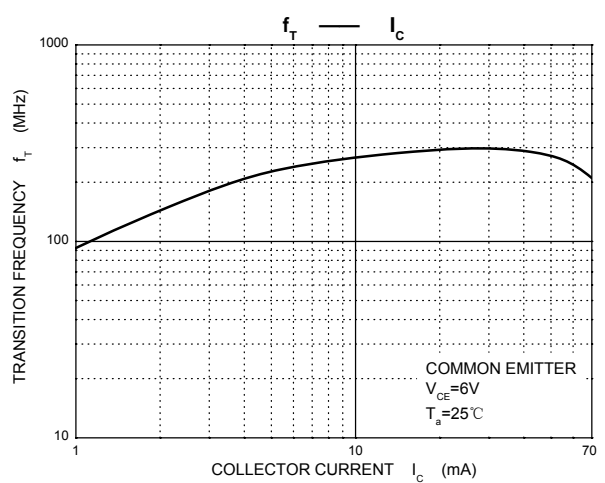
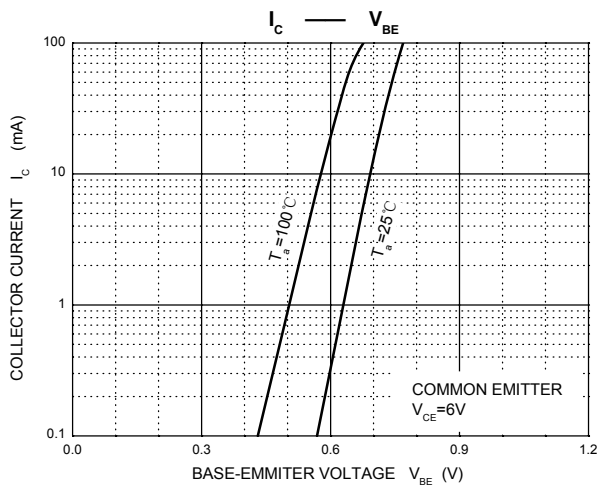
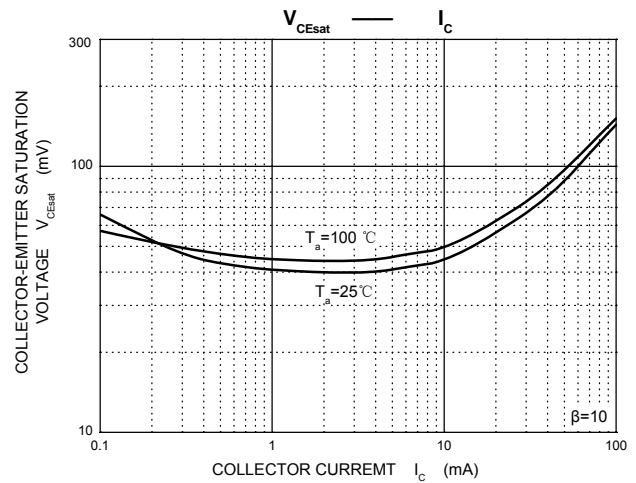
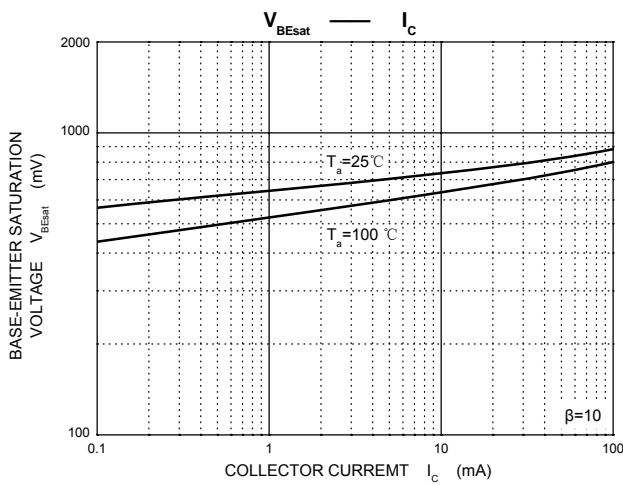
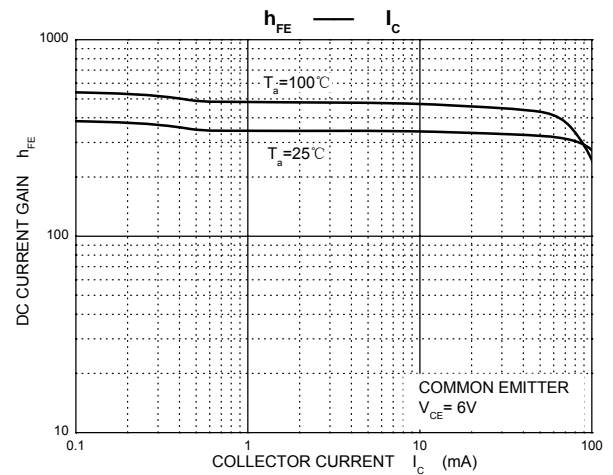
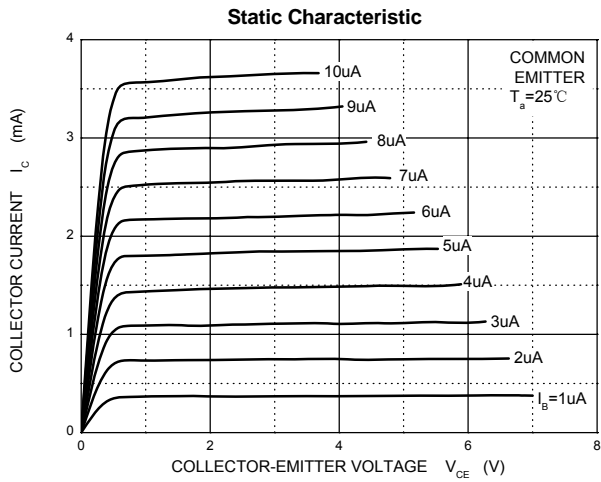
### ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=60V, I_E=0$			0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=5V, I_C=0$			0.1	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE}=6V, I_C=1\text{mA}$	90	200	600	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100\text{mA}, I_B=10\text{mA}$			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=100\text{mA}, I_B=10\text{mA}$			1	V
Transition frequency	$f_T$	$V_{CE}=6V, I_C=10\text{mA}$		250		MHz

### CLASSIFICATION OF $h_{FE}$

Rank	L4	L5	L6	L7
Range	90-180	135-270	200-400	300-600
Marking	L4	L5	L6	L7

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单击下面可查看定价，库存，交付和生命周期等信息

[>>UMW\(友台半导体\)](#)